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(54) THIN FILM TRANSISTOR SUBSTRATE AND METHOD OF FABRICATING THE SAME

(57) Abstract:

PURPOSE: A thin film transistor substrate and a method of fabricating the substrate are provided in which a color filter is directly formed on the thin film transistor substrate to improve aperture rate and the color filter is formed using electro-deposition to reduce the number of masks used for fabricating the thin film transistor.

CONSTITUTION: A thin film transistor substrate includes an insulating substrate, a plurality of gate lines(21) formed on the insulating substrate, and a plurality of data lines(61) intersecting the gate lines to define a plurality of pixel regions. The substrate further has a plurality of thin film transistors formed at the pixel regions and electrically connected to the data lines, a passivation film formed on the substrate, exposing the drain electrode of each thin film transistor, and polarizing plates(91,92,93) for electro-deposition placed in the pixel regions, exposing the drain electrode. The substrate also has a light-shielding layer(100) having an opening exposing the inner regions of the polarizing plates and a contact hole exposing the drain electrode, the first to third color filters(121,122,123) formed on the exposed region of the polarizing plate, and a plurality of pixel electrodes each of which is formed at each pixel region.

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Legal Status